PZT2907A TRANSISTOR (PNP)

SOT-223

1. BASE
2. COLLECTOR
3. EMITTER

FEATURES

Power dissipation

$P_{CM:}$ 1 W (Tamb=25℃)

Collector current

$I_{CM:}$ -0.6 A

Collector-base voltage

$V_{(BR)CBO:}$ -60 V

Operating and storage junction temperature range

$T_{J,}T_{stg:}$ -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=-100μA,I_E=0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=-1mA,I_B=0	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-50V,I_E=0			-10	nA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V,I_C=0			-50	nA
DC current gain	$h_{FE(1)}$	V_{CE}=-10V,I_C=-0.1mA	75			
	$h_{FE(2)}$	V_{CE}=-10V,I_C=-1mA	100			
	$h_{FE(3)}$	V_{CE}=-10V,I_C=-10mA	100			
	$h_{FE(4)}$	V_{CE}=-10V,I_C=-150mA	100		300	
	$h_{FE(5)}$	V_{CE}=-10V,I_C=-500mA	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-150mA,I_B=-15mA			-0.4	V
	$V_{CE(sat)}$	I_C=-500mA,I_B=-50mA			-1.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-150mA,I_B=-15mA			-1.3	V
	$V_{BE(sat)}$	I_C=-500mA,I_B=-50mA			-2.6	V
Transition frequency	f_T	V_{CE}=-20V,I_C=-50mA,f=100MHz	200			MHz
Collector capacitance	C_c	V_{CB}=-10V,I_E=0,f=1MHz			8	pF
Emitter capacitance	C_E	V_{EB}=-2V,I_C=0,f=1MHz			30	pF
Delay time	t_d	I_C=-150mA I_{B1}=- I_{B2}=- 15mA			12	nS
Rise time	t_r				30	nS
Storage time	t_S				300	nS
Fall time	t_f				65	nS